

# UP03397G

Silicon NPN epitaxial planar type (Tr1)  
 Silicon PNP epitaxial planar type (Tr2)

For digital circuits

■ Features

- Two elements incorporated into one package (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number

- UNR2154 + UNR2211

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	50	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
	Collector current	$I_C$	100	mA
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	-30	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	-30	V
	Collector current	$I_C$	-100	mA
Overall	Total power dissipation	$P_T$	125	mW
	Junction temperature	$T_j$	125	$^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

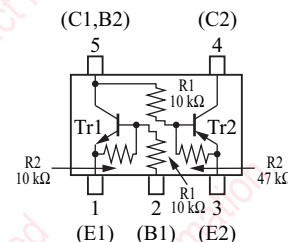
■ Package

- Code  
SSMini5-F3
- Pin Name
 

1: Emitter (Tr1)	4: Collector (Tr2)
2: Base (Tr1)	5: Collector (Tr1)
3: Emitter (Tr2)	Base (Tr2)

■ Marking Symbol: 3M

■ Internal Connection



■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

- Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 50 \text{ V}, I_B = 0$			0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_C = 0$			0.5	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	35			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$			0.25	V
Output voltage high-level	$V_{OH}$	$V_{CC} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	4.9			V
Output voltage low-level	$V_{OL}$	$V_{CC} = 5 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			0.2	V
Input resistance	$R_1$		-30%	10	+30%	$\text{k}\Omega$
Resistance ratio	$R_1 / R_2$		0.8	1.0	1.2	—
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

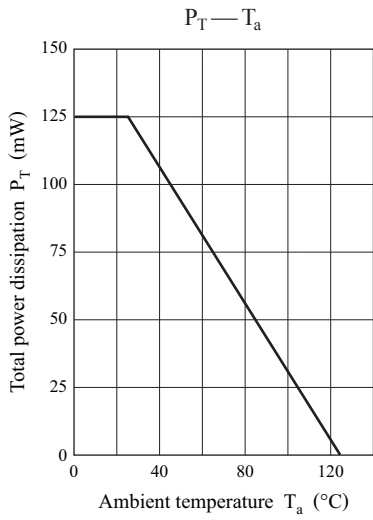
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

## • Tr2

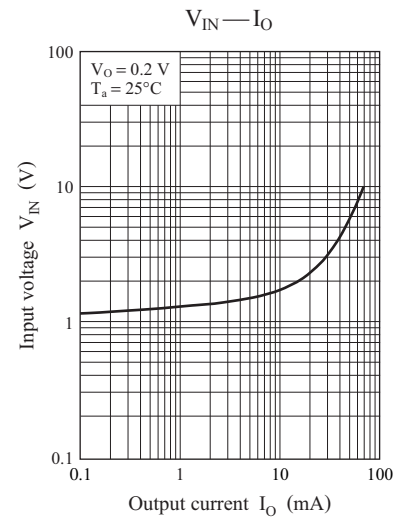
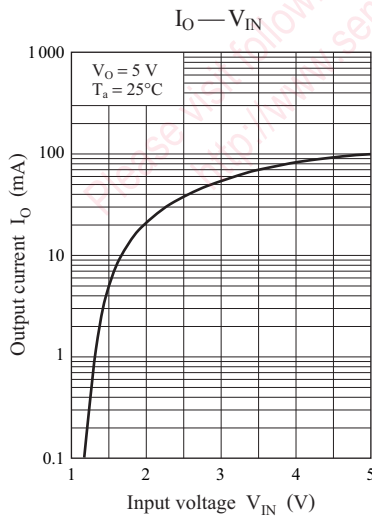
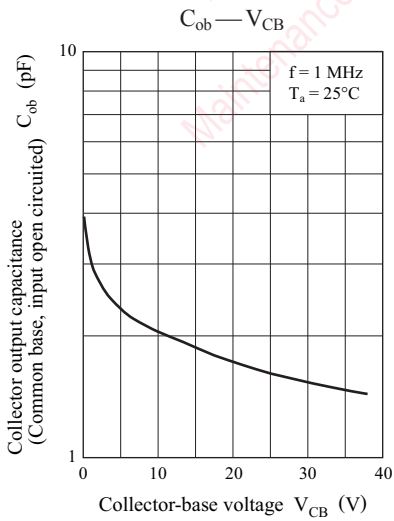
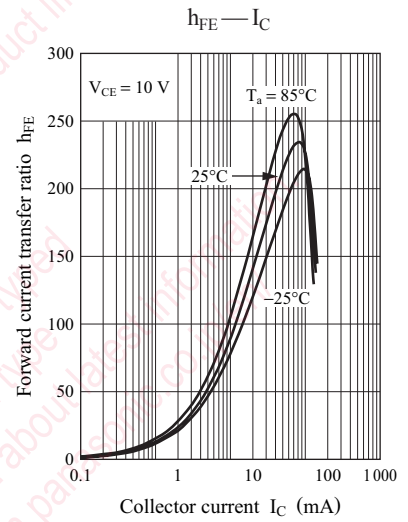
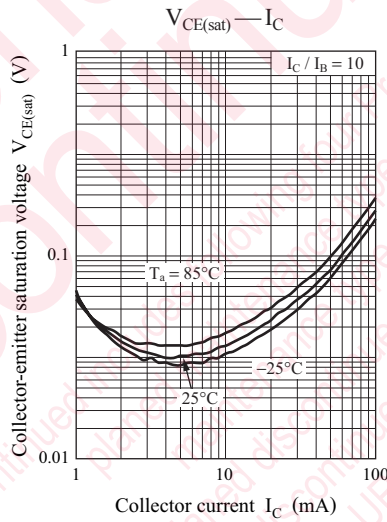
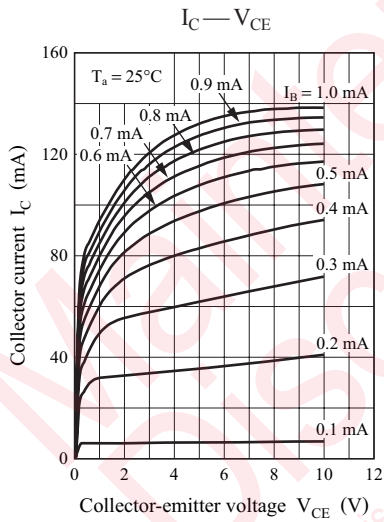
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -10 \mu A, I_E = 0$	-30			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -2 \text{ mA}, I_B = 0$	-30			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -30 \text{ V}, I_E = 0$			-0.1	$\mu A$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -30 \text{ V}, I_B = 0$			-0.5	$\mu A$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -3 \text{ V}, I_C = 0$			-0.1	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	80			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50 \text{ mA}, I_B = -0.33 \text{ mA}$			-1.2	V
Output voltage high-level	$V_{OH}$	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	$V_{OL}$	$V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			-0.2	V
Input resistance	$R_1$		-30%	10	+30%	$\text{k}\Omega$
Resistance ratio	$R_1 / R_2$			0.213		—
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

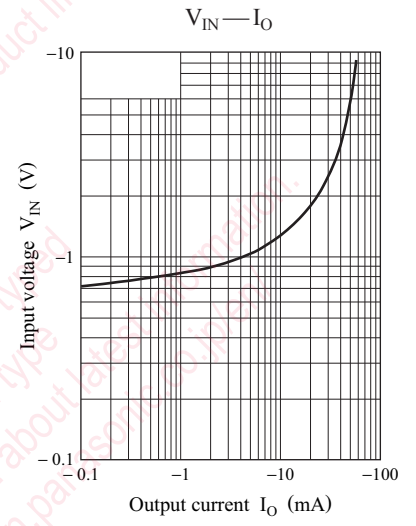
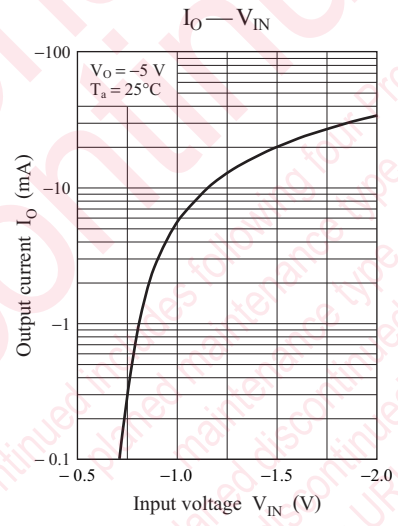
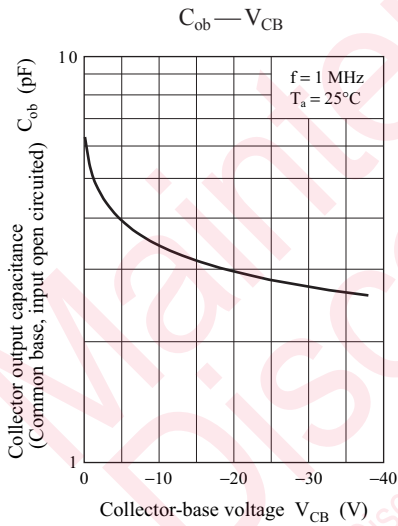
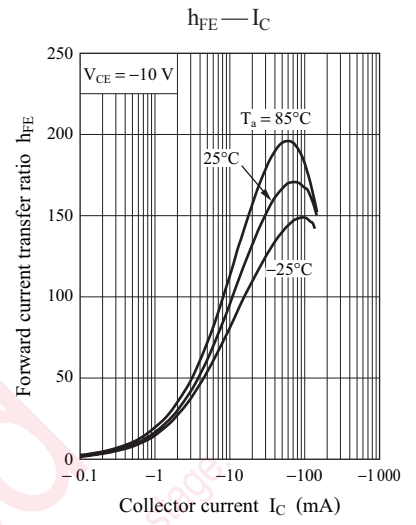
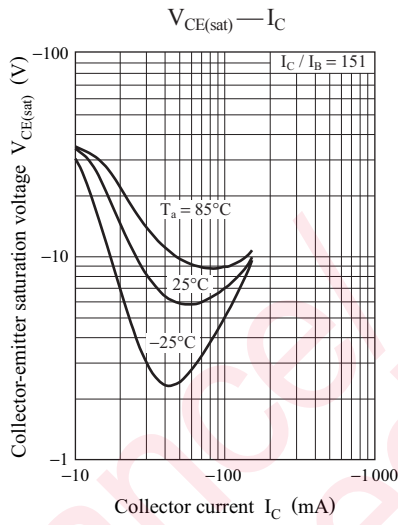
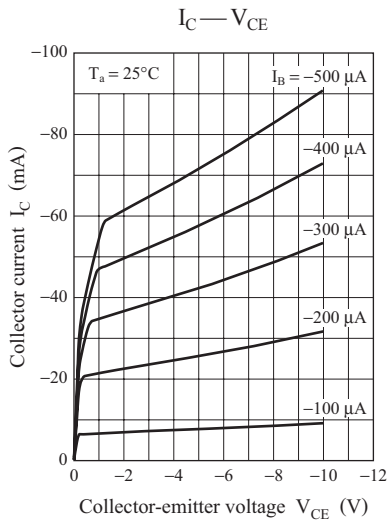
Common characteristics chart



Characteristics charts of Tr1

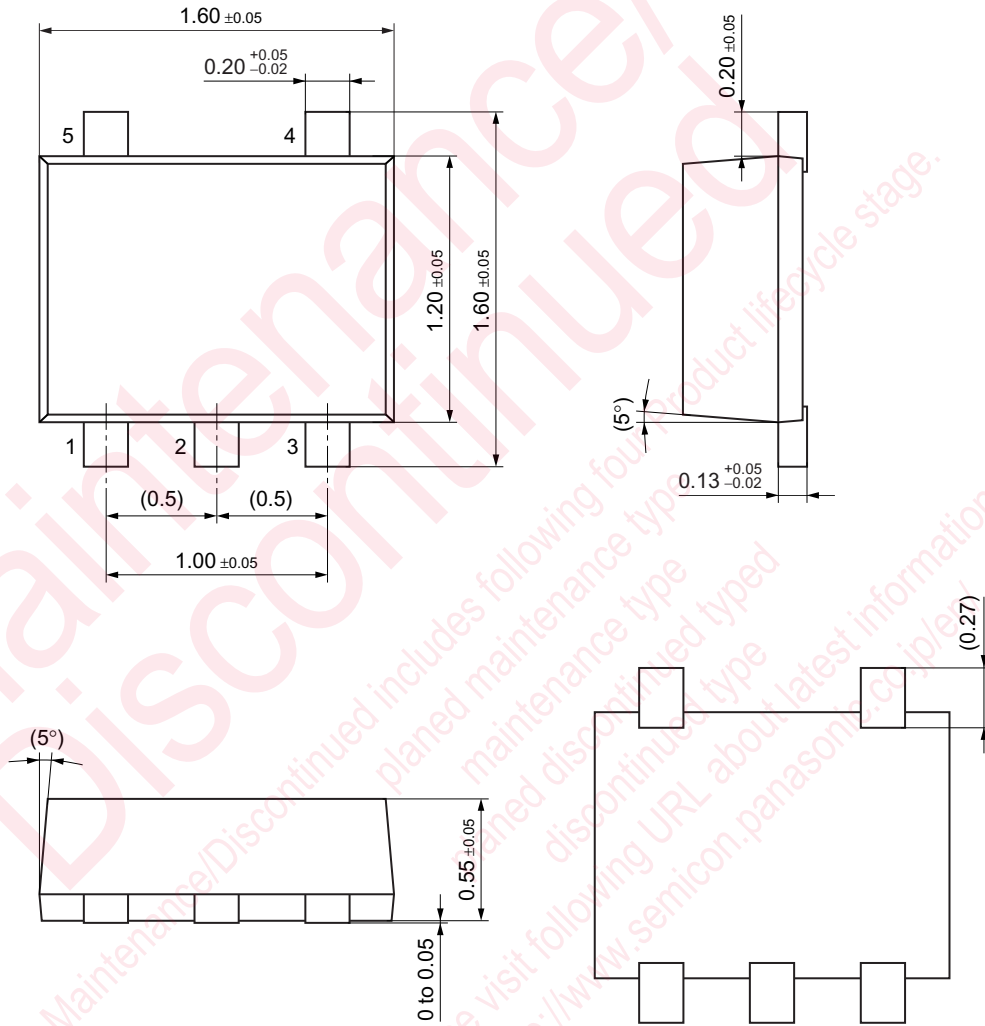


Characteristics charts of Tr2



SSMini5-F3

Unit: mm



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